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FAIRCHILD

SEMICONDUCTOR®

ISL9V3040D3S / ISL9V3040S3S / ISL9V3040P3 / ISL9V3040S3

EcoSPARK® 300mJ, 400V, N-Channel Ignition IGBT

General Description

The ISL9V3040D3S, ISL9V3040S3S, ISL9V3040P3, and ISL9V3040S3 are the next generation ignition IGBTs that offer outstanding SCIS capability in the space saving D-Pak (TO-252), as well as the industry standard D²-Pak (TO-263), and TO-262 and TO-220 plastic packages. This device is intended for use in automotive ignition circuits, specifically as a coil driver. Internal diodes provide voltage clamping without the need for external components.

EcoSPARK® devices can be custom made to specific clamp voltages. Contact your nearest Fairchild sales office for more information.
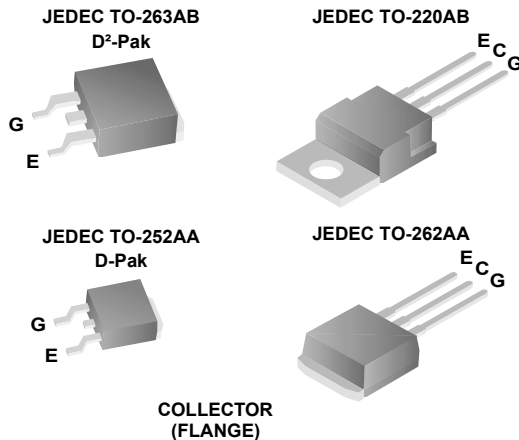
Formerly Developmental Type 49362

Applications

- Automotive Ignition Coil Driver Circuits
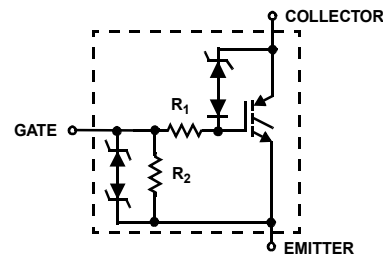- Coil- On Plug Applications

Features

- Space saving D-Pak package availability
- SCIS Energy = 300mJ at T_J = 25°C
- Logic Level Gate Drive

Package

JEDEC TO-263AB
D²-Pak

G

E

JEDEC TO-252AA
D-Pak

G

E

COLLECTOR
(FLANGE)

JEDEC TO-220AB

E C G

JEDEC TO-262AA

E C G

Symbol

Device Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
BV_{CER}	Collector to Emitter Breakdown Voltage (I_C = 1 mA)	430	V
BV_{ECS}	Emitter to Collector Voltage - Reverse Battery Condition (I_C = 10 mA)	24	V
E_{SCIS25}	At Starting T_J = 25°C, I_{SCIS} = 14.2A, L = 3.0 mHy	300	mJ
$E_{SCIS150}$	At Starting T_J = 150°C, I_{SCIS} = 10.6A, L = 3.0 mHy	170	mJ
I_{C25}	Collector Current Continuous, At T_C = 25°C, See Fig 9	21	A
I_{C110}	Collector Current Continuous, At T_C = 110°C, See Fig 9	17	A
V_{GEM}	Gate to Emitter Voltage Continuous	±10	V
P_D	Power Dissipation Total T_C = 25°C	150	W
	Power Dissipation Derating T_C > 25°C	1.0	W/°C
T_J	Operating Junction Temperature Range	-40 to 175	°C
T_{STG}	Storage Junction Temperature Range	-40 to 175	°C
T_L	Max Lead Temp for Soldering (Leads at 1.6mm from Case for 10s)	300	°C
T_{pkg}	Max Lead Temp for Soldering (Package Body for 10s)	260	°C
ESD	Electrostatic Discharge Voltage at 100pF, 1500Ω	4	kV

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
V3040D	ISL9V3040D3ST	TO-252AA	330mm	16mm	2500
V3040S	ISL9V3040S3ST	TO-263AB	330mm	24mm	800
V3040P	ISL9V3040P3	TO-220AB	Tube	N/A	50
V3040S	ISL9V3040S3	TO-262AA	Tube	N/A	50
V3040D	ISL9V3040D3S	TO-252AA	Tube	N/A	75
V3040S	ISL9V3040S3S	TO-263AB	Tube	N/A	50

Electrical Characteristics T_A = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions		Min	Typ	Max	Units
Off State Characteristics							
BV_{CER}	Collector to Emitter Breakdown Voltage	I_C = 2mA, V_{GE} = 0, R_G = 1KΩ See Fig. 15 T_J = -40 to 150°C		370	400	430	V
BV_{CES}	Collector to Emitter Breakdown Voltage	I_C = 10mA, V_{GE} = 0, R_G = 0, See Fig. 15 T_J = -40 to 150°C		390	420	450	V
BV_{ECS}	Emitter to Collector Breakdown Voltage	I_C = -75mA, V_{GE} = 0V, T_C = 25°C		30	-	-	V
BV_{GES}	Gate to Emitter Breakdown Voltage	I_{GES} = ± 2mA		±12	±14	-	V
I_{CER}	Collector to Emitter Leakage Current	V_{CER} = 250V, R_G = 1KΩ, See Fig. 11	T_C = 25°C	-	-	25	µA
			T_C = 150°C	-	-	1	mA
I_{ECS}	Emitter to Collector Leakage Current	V_{EC} = 24V, See Fig. 11	T_C = 25°C	-	-	1	mA
			T_C = 150°C	-	-	40	mA
R_1	Series Gate Resistance			-	70	-	Ω
R_2	Gate to Emitter Resistance			10K	-	26K	Ω
On State Characteristics							
$V_{CE(SAT)}$	Collector to Emitter Saturation Voltage	I_C = 6A, V_{GE} = 4V	T_C = 25°C, See Fig. 3	-	1.25	1.60	V
$V_{CE(SAT)}$	Collector to Emitter Saturation Voltage	I_C = 10A, V_{GE} = 4.5V	T_C = 150°C, See Fig. 4	-	1.58	1.80	V
$V_{CE(SAT)}$	Collector to Emitter Saturation Voltage	I_C = 15A, V_{GE} = 4.5V	T_C = 150°C	-	1.90	2.20	V
Dynamic Characteristics							
$Q_{G(ON)}$	Gate Charge	I_C = 10A, V_{CE} = 12V, V_{GE} = 5V, See Fig. 14		-	17	-	nC
$V_{GE(TH)}$	Gate to Emitter Threshold Voltage	I_C = 1.0mA, V_{CE} = V_{GE}, See Fig. 10	T_C = 25°C	1.3	-	2.2	V
			T_C = 150°C	0.75	-	1.8	V
V_{GEP}	Gate to Emitter Plateau Voltage	I_C = 10A, V_{CE} = 12V		-	3.0	-	V
Switching Characteristics							
$t_{d(ON)R}$	Current Turn-On Delay Time-Resistive	V_{CE} = 14V, R_L = 1Ω, V_{GE} = 5V, R_G = 1KΩ T_J = 25°C, See Fig. 12		-	0.7	4	µs
t_{rR}	Current Rise Time-Resistive			-	2.1	7	µs
$t_{d(OFF)L}$	Current Turn-Off Delay Time-Inductive	V_{CE} = 300V, L = 500µHy, V_{GE} = 5V, R_G = 1KΩ T_J = 25°C, See Fig. 12		-	4.8	15	µs
t_{fL}	Current Fall Time-Inductive			-	2.8	15	µs
SCIS	Self Clamped Inductive Switching	T_J = 25°C, L = 3.0 mHy, R_G = 1KΩ, V_{GE} = 5V, See Fig. 1 & 2		-	-	300	mJ
Thermal Characteristics							
$R_{\theta JC}$	Thermal Resistance Junction-Case	All packages		-	-	1.0	°C/W

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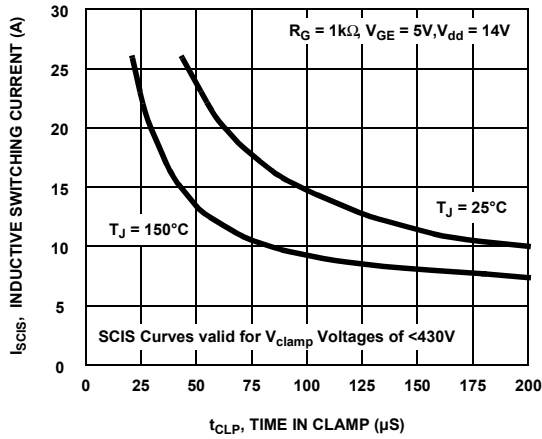# Typical Performance Curves

Figure 1. Self Clamped Inductive Switching Current vs Time in Clamp
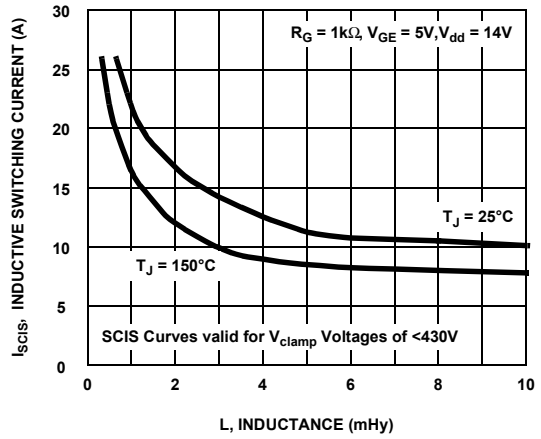

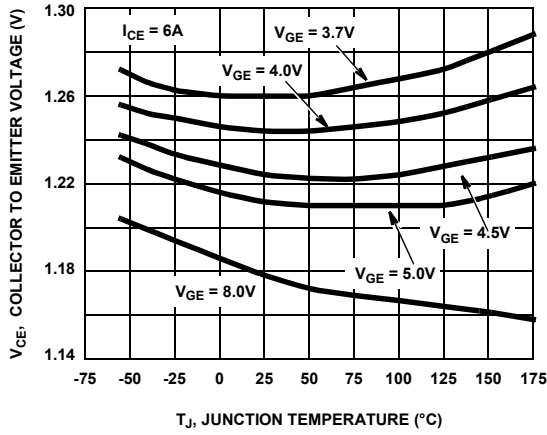Figure 2. Self Clamped Inductive Switching Current vs Inductance

Figure 3. Collector to Emitter On-State Voltage vs Junction Temperature
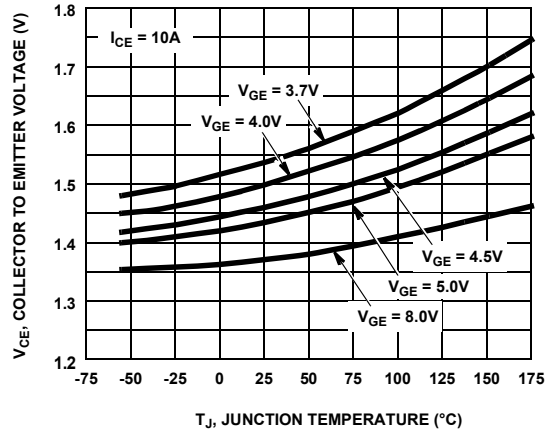

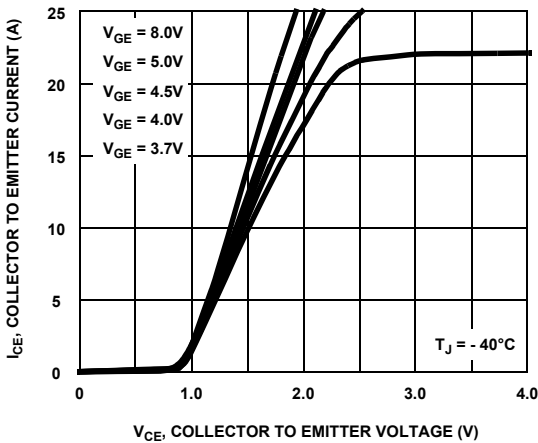Figure 4. Collector to Emitter On-State Voltage vs Junction Temperature

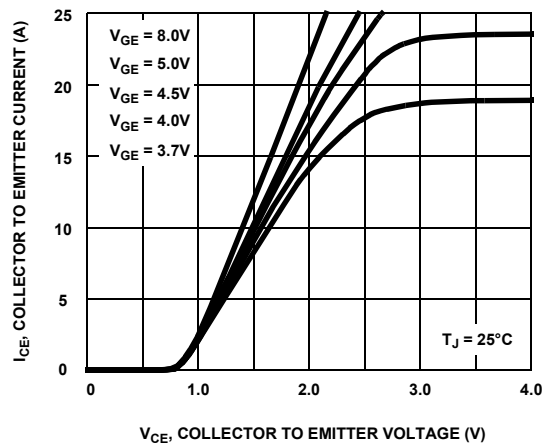Figure 5. Collector to Emitter On-State Voltage vs Collector Current

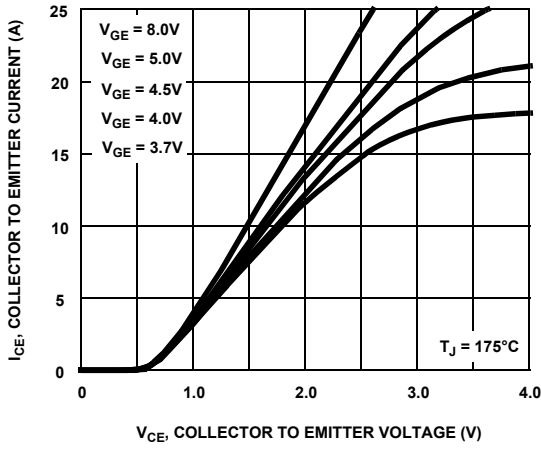Figure 6. Collector to Emitter On-State Voltage vs Collector Current

Typical Performance Curves (Continued)

Figure 7. Collector to Emitter On-State Voltage vs Collector Current
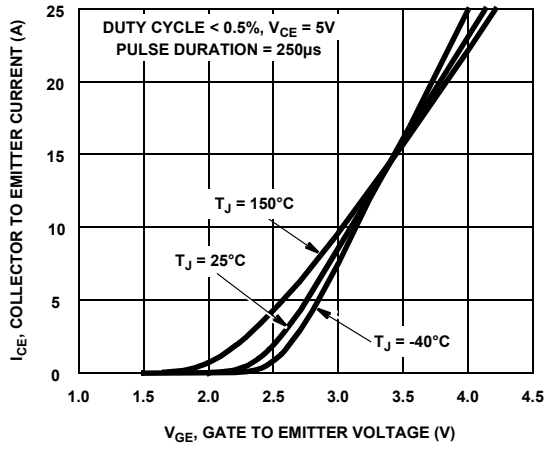
Figure 8. Transfer Characteristics
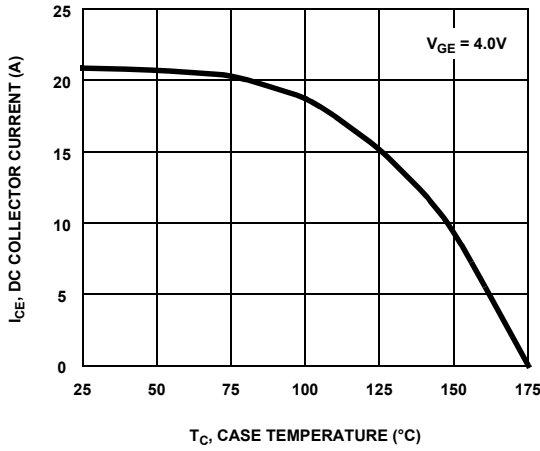
Figure 9. DC Collector Current vs Case Temperature
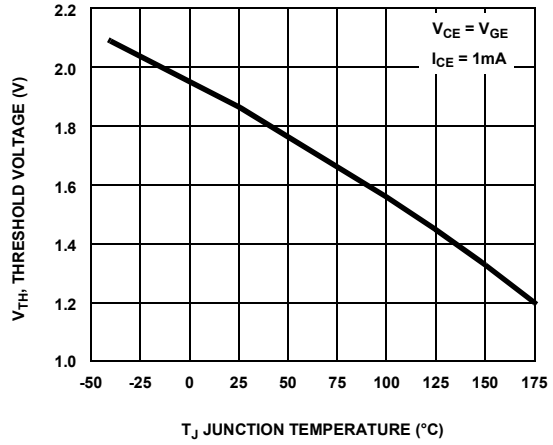
Figure 10. Threshold Voltage vs Junction Temperature
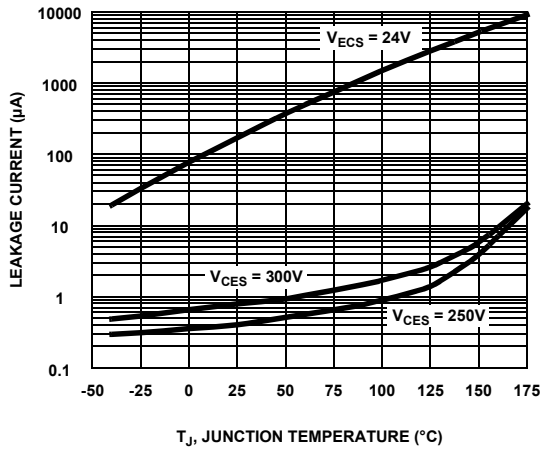
Figure 11. Leakage Current vs Junction Temperature
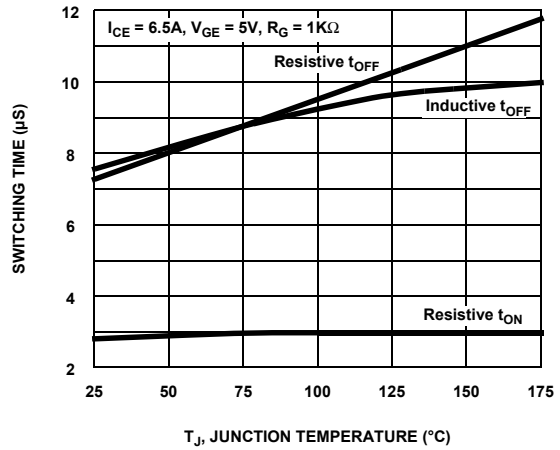
Figure 12. Switching Time vs Junction Temperature

Typical Performance Curves (Continued)
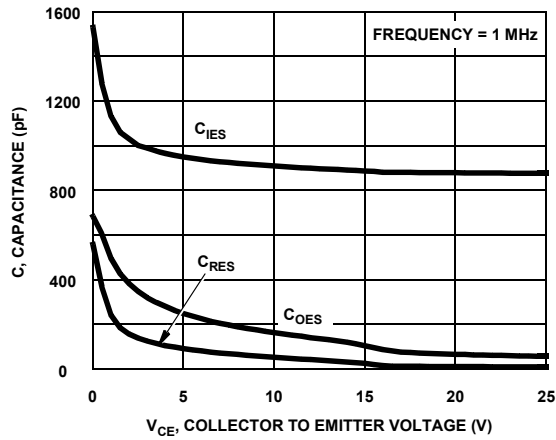
Figure 13. Capacitance vs Collector to Emitter Voltage
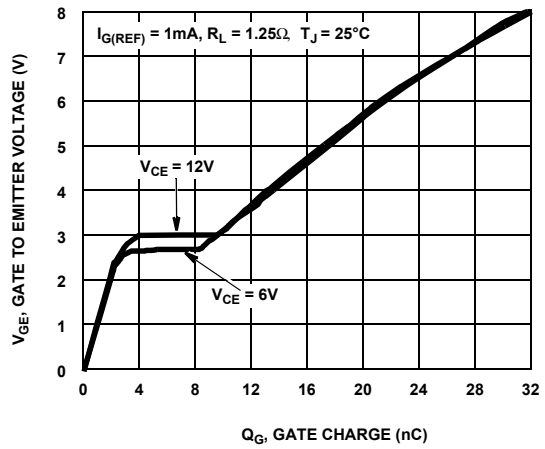
Figure 14. Gate Charge
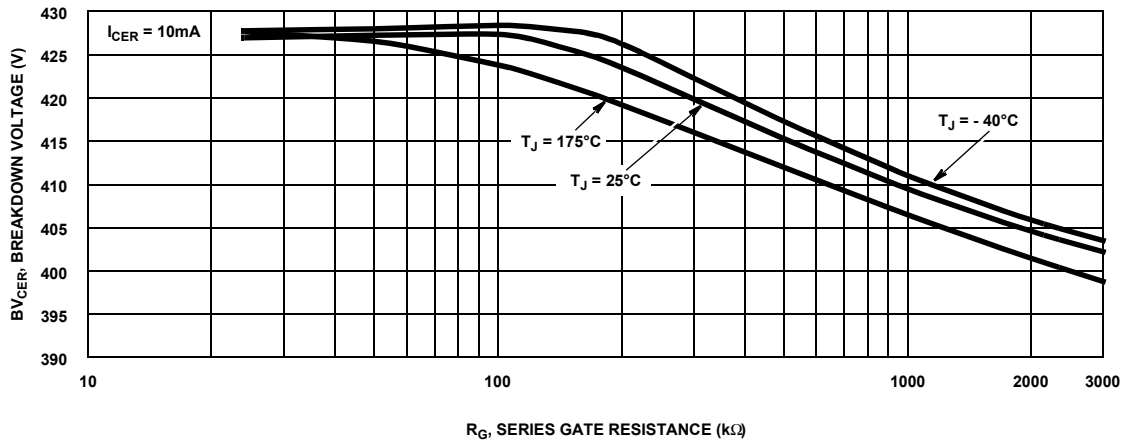
Figure 15. Breakdown Voltage vs Series Gate Resistance

DUTY FACTOR, D = t_1 / t_2
PEAK T_J = (P_D X $Z_{\theta JC}$ X $R_{\theta JC}$) + T_C
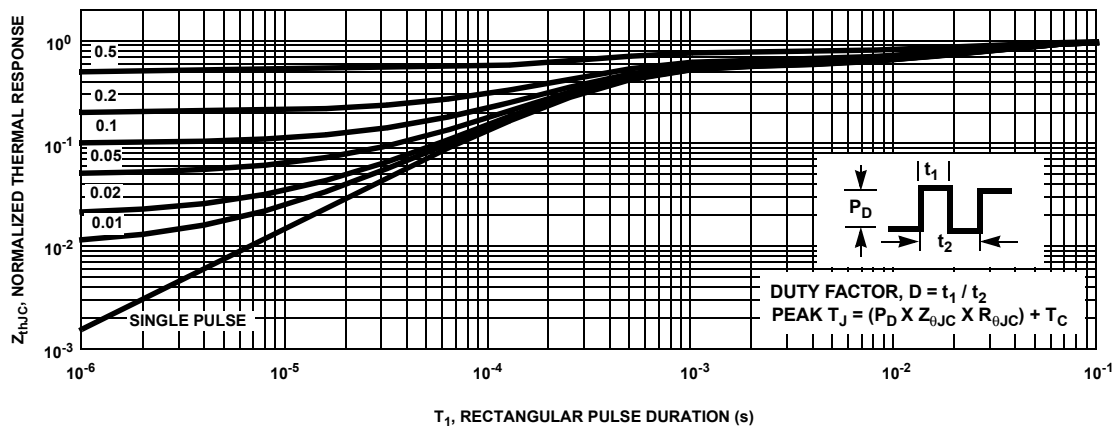
Figure 16. IGBT Normalized Transient Thermal Impedance, Junction to Case

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Test Circuit and Waveforms
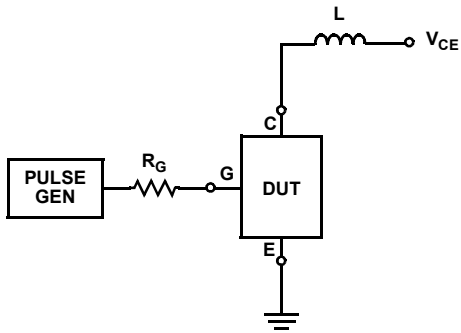
Figure 17. Inductive Switching Test Circuit
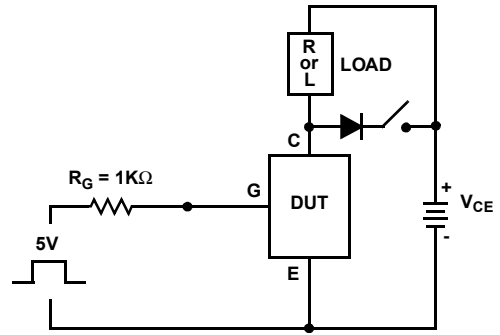
Figure 18. t_{ON} and t_{OFF} Switching Test Circuit
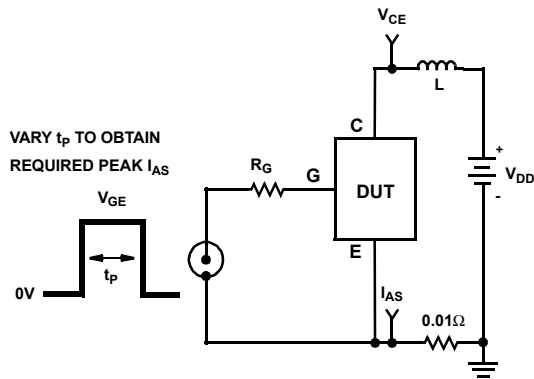
Figure 19. Energy Test Circuit
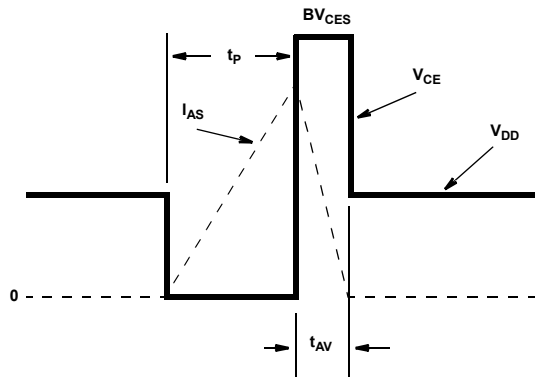
Figure 20. Energy Waveforms

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SPICE Thermal Model

REV 7 March 2002

ISL9V3040D3S / ISL9V3040S3S / ISL9V3040P3 / ISL9V3040S3

CTHERM1 th 6 2.1e -3
CTHERM2 6 5 1.4e -1
CTHERM3 5 4 7.3e -3
CTHERM4 4 3 2.1e -1
CTHERM5 3 2 1.1e -1
CTHERM6 2 tl 6.2e +6

RTHERM1 th 6 1.2e -1
RTHERM2 6 5 1.9e -1
RTHERM3 5 4 2.2e -1
RTHERM4 4 3 6.0e -2
RTHERM5 3 2 5.8e -2
RTHERM6 2 tl 1.6e -3

SABER Thermal Model

SABER thermal model
ISL9V3040D3S / ISL9V3040S3S / ISL9V3040P3 / ISL9V3040S3
template thermal_model th tl
thermal_c th, tl
{
ctherm.ctherm1 th 6 = 2.1e -3
ctherm.ctherm2 6 5 = 1.4e -1
ctherm.ctherm3 5 4 = 7.3e -3
ctherm.ctherm4 4 3 = 2.2e -1
ctherm.ctherm5 3 2 =1.1e -1
ctherm.ctherm6 2 tl = 6.2e +6

rtherm.rtherm1 th 6 = 1.2e -1
rtherm.rtherm2 6 5 = 1.9e -1
rtherm.rtherm3 5 4 = 2.2e -1
rtherm.rtherm4 4 3 = 6.0e -2
rtherm.rtherm5 3 2 = 5.8e -2
rtherm.rtherm6 2 tl = 1.6e -3
}

th ○ JUNCTION

RTHERM1   CTHERM1

6

RTHERM2   CTHERM2

5

RTHERM3   CTHERM3

4

RTHERM4   CTHERM4

3

RTHERM5   CTHERM5

2

RTHERM6   CTHERM6

tl ○ CASE

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